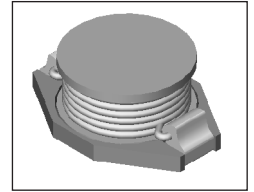


# SMT Power Inductor

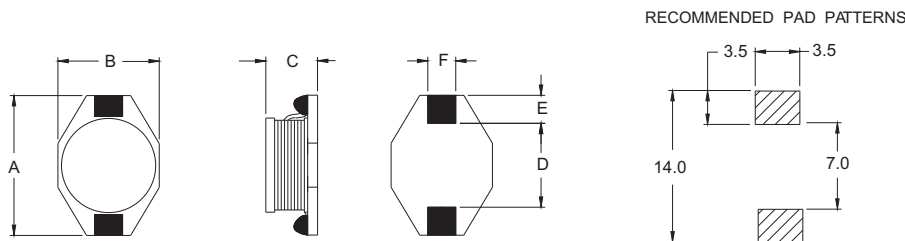
## SISH811 Type

### Features

- RoHS compliant.
- High current (3.5A, 10uH), SMD type.
- Unshielded.
- Self-leads, suitable for high density mounting.
- High energy storage and low DCR.
- Provided with embossed carrier tape packing.
- Ideal for power source circuits, DC-DC converter, DC-AC inverters inductor applications.
- In addition to the standard versions shown here, customized inductors are available to meet your exact requirements.



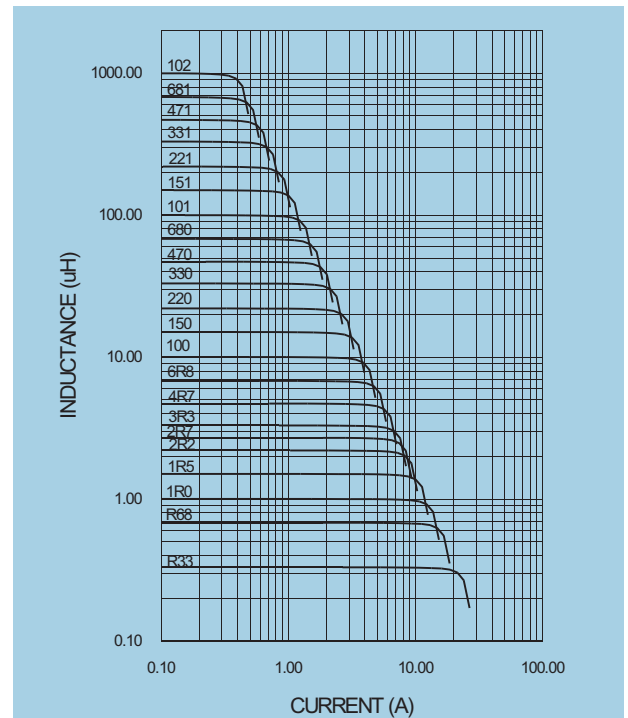
### Mechanical Dimension:



UNIT:mm/inch  
 A = 12.94 / 0.510 Max.  
 B = 9.4 / 0.370 Max.  
 C = 11.4 / 0.449 Max.  
 D = 7.7±0.2 / 0.311±0.008  
 E = 2.5±0.2 / 0.098±0.008  
 F = 2.5±0.2 / 0.098±0.008

### Electrical Characteristics: 25°C: 100KHz, 0.1V

| PART NO.      | $L^1$<br>(uH) | DCR<br>( $\Omega$ )MAX | $Isat^2$<br>(A dc) | $I_r^3$<br>(A dc) |
|---------------|---------------|------------------------|--------------------|-------------------|
| SISH811 - 2R2 | 2.2           | 0.006                  | 17.0               | 9.0               |
| SISH811 - 3R3 | 3.3           | 0.010                  | 14.0               | 7.0               |
| SISH811 - 4R7 | 4.7           | 0.013                  | 11.0               | 6.0               |
| SISH811 - 100 | 10.0          | 0.040                  | 8.0                | 3.5               |
| SISH811 - 150 | 15.0          | 0.050                  | 7.0                | 3.0               |
| SISH811 - 220 | 22.0          | 0.066                  | 5.5                | 2.5               |
| SISH811 - 330 | 33.0          | 0.080                  | 4.0                | 2.0               |
| SISH811 - 470 | 47.0          | 0.110                  | 3.8                | 1.6               |
| SISH811 - 680 | 68.0          | 0.170                  | 3.0                | 1.2               |
| SISH811 - 101 | 100.0         | 0.220                  | 2.5                | 1.2               |
| SISH811 - 151 | 150.0         | 0.340                  | 2.0                | 0.9               |
| SISH811 - 221 | 220.0         | 0.440                  | 1.6                | 0.7               |
| SISH811 - 331 | 330.0         | 0.700                  | 1.2                | 0.6               |
| SISH811 - 471 | 470.0         | 0.950                  | 1.0                | 0.3               |
| SISH811 - 681 | 680.0         | 1.200                  | 1.0                | 0.2               |
| SISH811 - 102 | 1000.0        | 2.000                  | 0.8                | 0.1               |



1. Tolerance of inductance:  $\pm 20\%$ .
2.  $Isat$  is the DC current which cause the inductance drop less than 10% of its nominal inductance without current.
3.  $I_r$  is the DC current which cause the surface temperature of the part increase less than 45°C.
4. Operating temperature : -20°C to 105°C (including self-temperature rise)



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